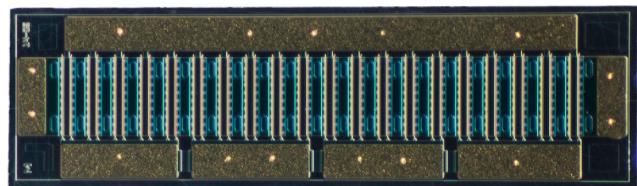


# CG2H80060D

60 W, 8.0 GHz, GaN HEMT Die

## Description

Wolfspeed's CG2H80060D is a gallium nitride (GaN) High Electron Mobility Transistor (HEMT). GaN has superior properties compared to silicon or gallium arsenide, including higher breakdown voltage, higher saturated electron drift velocity, and higher thermal conductivity. GaN HEMTs offer greater power density and wider bandwidths compared to Si and GaAs transistors.



PNs: CG2H80060D

## Features

- 15 dB Typical Small Signal Gain at 4 GHz
- 12 dB Typical Small Signal Gain at 8 GHz
- 60 W Typical  $P_{SAT}$
- 28 V Operation
- High Breakdown Voltage
- High Temperature Operation
- Up to 8 GHz Operation
- High Efficiency

## Applications

- 2-Way Private Radio
- Broadband Amplifiers
- Cellular Infrastructure
- Test Instrumentation
- Class A, AB, Linear amplifiers suitable for OFDM, W-CDMA, EDGE, CDMA waveforms

## Packaging Information



- Bare die are shipped in Gel-Pak® containers
- Non-adhesive tacky membrane immobilizes die during shipment



**Large Signal Models Available for ADS and MWO**



## Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	$V_{DSS}$	120	V	25°C
Gate-to-Source Voltage	$V_{GS}$	-10, +2		
Storage Temperature	$T_{STG}$	-65, +150	°C	
Operating Junction Temperature	$T_J$	225		
Maximum Forward Gate Current	$I_{GMAX}$	15	mA	25°C
Maximum Drain Current <sup>1</sup>	$I_{DMAX}$	6	A	
Thermal Resistance, Junction to Case (packaged) <sup>2</sup>	$R_{\theta JC}$	2.8	°C/W	85°C
Thermal Resistance, Junction to Case (die only)		1.5		
Mounting Temperature (30 seconds)	$T_s$	320	°C	30 seconds

Notes:

<sup>1</sup> Current limit for long term, reliable operation

<sup>2</sup> Eutectic die attach using 80/20 AuSn mounted to a 60 mil thick CuMoCu carrier

## Electrical Characteristics (Frequency = 4 GHz unless otherwise stated; $T_c = 25^\circ C$ )

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>DC Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	$V_{DC}$	$V_{DS} = 10 V, I_D = 14.4 \text{ mA}$
Gate Quiescent Voltage	$V_{GS(Q)}$	—	-2.7	—		$V_{DD} = 28 V, I_{DQ} = 400 \text{ mA}$
Drain Current	$I_{DSS}$	11.6	14.0	—	A	$V_{DS} = 6.0 V, V_{GS} = 2.0 V$
Drain-Source Breakdown Voltage	$V_{BD}$	120	—	—	V	$V_{GS} = -8 V, I_D = 14.4 \text{ mA}$
On Resistance	$R_{ON}$	—	0.17	—	$\Omega$	$V_{DS} = 0.10 V$
Gate Forward Voltage	$V_{G-ON}$	—	1.9	—	V	$I_{GS} = 14.4 \text{ mA}$
<b>RF Characteristics</b>						
Small Signal Gain	$G_{SS}$	—	15	—	dB	$V_{DD} = 28 V, I_{DQ} = 400 \text{ mA}$
Saturated Output Power <sup>1</sup>	$P_{SAT}$	—	60	—	W	
Drain Efficiency <sup>2</sup>	$\eta$	—	65	—	%	$V_{DD} = 28 V, I_{DQ} = 400 \text{ mA}, P_{SAT} = 60 W$
Intermodulation Distortion	IM3	—	-30	—	dBc	$V_{DD} = 28 V, I_{DQ} = 400 \text{ mA}, P_{OUT} = 60 W \text{ PEP}$
Output Mismatch Stress <sup>3</sup>	VSWR	—	—	10 : 1	Y	$V_{DD} = 28 V, I_{DQ} = 400 \text{ mA}, P_{OUT} = 60 W \text{ (CW)}$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{GS}$	—	14.7	—	pF	$V_{DS} = 28 V, V_{GS} = -8 V, f = 1 \text{ MHz}$
Output Capacitance	$C_{DS}$	—	4.4	—		
Feedback Capacitance	$C_{GD}$	—	0.8	—		

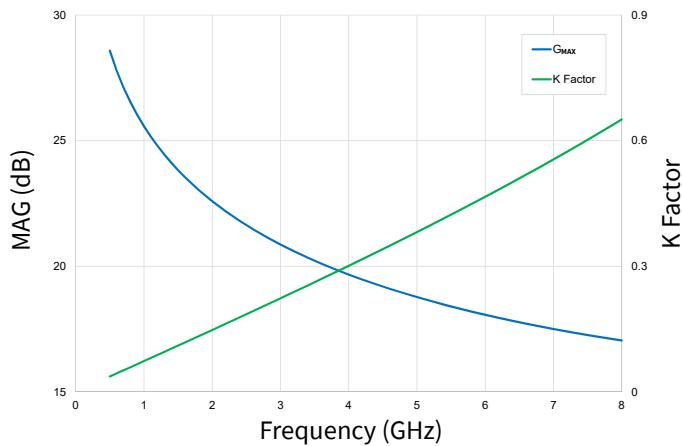
Notes:

<sup>1</sup>  $P_{SAT}$  is defined as  $I_G = 0.7 \text{ mA}$

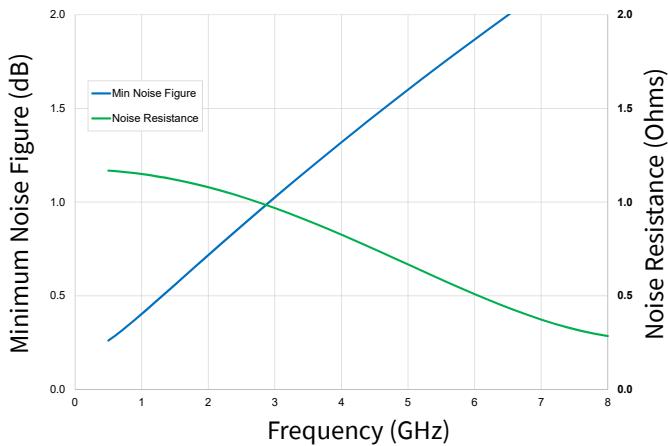
<sup>2</sup> Drain Efficiency =  $P_{OUT} / P_{DC}$

<sup>3</sup> No damage at all phase angles

## Typical Performance



**Figure 1.** Simulated Maximum Available Gain and K Factor  
 $V_{DD} = 28$  V,  $I_{DQ} = 400$  mA



**Figure 2.** Simulated Minimum Noise Figure and Noise Resistance vs. Frequency  
 $V_{DD} = 28$  V,  $I_{DQ} = 400$  mA

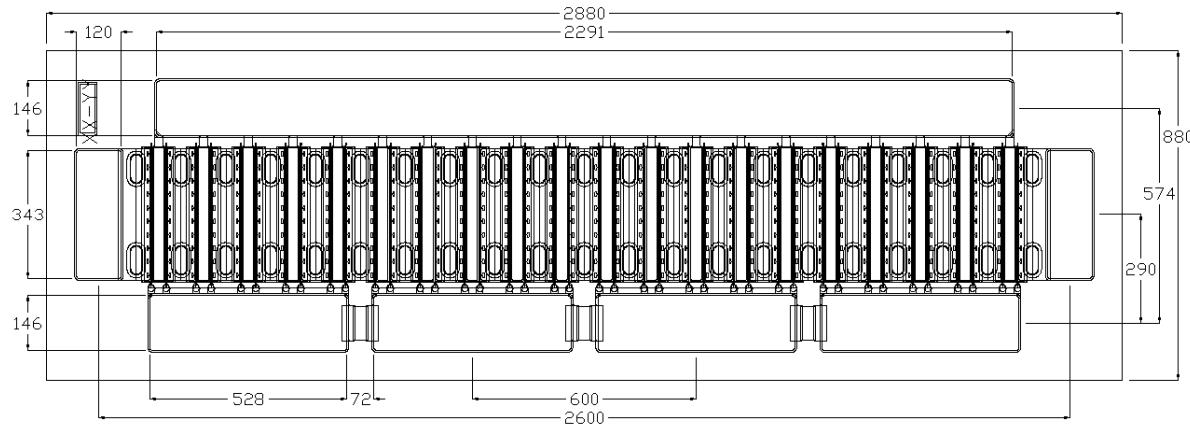
Intrinsic die parameters - reference planes at centers of gate and drain bonding pads. No wire bonds assumed.

## Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Classification Level	Test Methodology
Human Body Model	HBM	TBD	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 A114-D



## Die Dimensions (units in microns)



Overall die size 2880 x 880 (+0/-50) microns, die thickness 100 (+/- 10) microns.  
All Gate and Drain pads must be wire bonded for electrical connection

## Assembly Notes:

- Recommended solder is AuSn (80/20) solder. Refer to Wolfspeed's website for the Eutectic Die Bond Procedure application note at <https://www.wolfspeed.com/rf/document-library>
- Vacuum collet is the preferred method of pick-up.
- The backside of the die is the Source (ground) contact.
- Die back side gold plating is 5 microns thick minimum.
- Thermosonic ball or wedge bonding are the preferred connection methods.
- Gold wire must be used for connections.
- Use the die label (XX-YY) for correct orientation.

**Typical Package S-Parameters for CG2H80060D  
(Small Signal,  $V_{DS} = 28$  V,  $I_{DQ} = 400$  mA, magnitude/angle)**

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
0.5	0.940	-168.07	9.42	88.99	0.013	-0.29	0.735	-172.83
0.6	0.940	-169.98	7.85	86.72	0.013	-2.42	0.738	-173.30
0.7	0.941	-171.35	6.71	84.72	0.013	-4.27	0.740	-173.54
0.8	0.941	-172.36	5.86	82.90	0.013	-5.95	0.743	-173.64
0.9	0.941	-173.15	5.19	81.20	0.013	-7.51	0.745	-173.64
1.0	0.942	-173.77	4.66	79.58	0.013	-8.98	0.748	-173.59
1.1	0.942	-174.28	4.21	78.04	0.013	-10.38	0.750	-173.50
1.2	0.942	-174.70	3.85	76.54	0.013	-11.73	0.753	-173.38
1.3	0.943	-175.06	3.53	75.10	0.013	-13.03	0.756	-173.25
1.4	0.944	-175.36	3.26	73.69	0.013	-14.30	0.759	-173.10
1.5	0.944	-175.62	3.03	72.31	0.013	-15.53	0.763	-172.96
1.6	0.945	-175.85	2.82	70.97	0.012	-16.73	0.766	-172.81
1.8	0.946	-176.24	2.48	68.37	0.012	-19.04	0.773	-172.53
2.0	0.947	-176.55	2.20	65.86	0.012	-21.26	0.781	-172.28
2.2	0.949	-176.81	1.97	63.45	0.012	-23.38	0.788	-172.05
2.4	0.950	-177.03	1.78	61.12	0.012	-25.42	0.796	-171.87
2.6	0.952	-177.23	1.61	58.88	0.011	-27.37	0.803	-171.72
2.8	0.953	-177.41	1.47	56.72	0.011	-29.24	0.811	-171.61
3.0	0.955	-177.57	1.35	54.64	0.011	-31.03	0.819	-171.54
3.2	0.956	-177.73	1.24	52.63	0.011	-32.75	0.826	-171.50
3.4	0.958	-177.87	1.15	50.70	0.011	-34.39	0.833	-171.49
3.6	0.959	-178.02	1.06	48.84	0.010	-35.96	0.840	-171.51
3.8	0.960	-178.15	0.99	47.04	0.010	-37.46	0.847	-171.55
4.0	0.962	-178.28	0.92	45.32	0.010	-38.90	0.854	-171.61
4.2	0.963	-178.41	0.86	43.65	0.010	-40.27	0.860	-171.69
4.4	0.964	-178.54	0.80	42.05	0.009	-41.58	0.866	-171.78
4.6	0.965	-178.67	0.75	40.50	0.009	-42.83	0.871	-171.89
4.8	0.967	-178.79	0.71	39.01	0.009	-44.02	0.877	-172.01
5.0	0.968	-178.91	0.67	37.57	0.009	-45.16	0.882	-172.14
5.2	0.969	-179.03	0.63	36.18	0.009	-46.25	0.887	-172.27
5.4	0.970	-179.15	0.60	34.85	0.008	-47.29	0.892	-172.42
5.6	0.970	-179.27	0.56	33.55	0.008	-48.29	0.896	-172.57
5.8	0.971	-179.39	0.53	32.30	0.008	-49.23	0.900	-172.72
6.0	0.972	-179.51	0.51	31.10	0.008	-50.14	0.904	-172.87
6.2	0.973	-179.62	0.48	29.93	0.008	-51.00	0.908	-173.03
6.4	0.974	-179.74	0.46	28.80	0.008	-51.83	0.911	-173.19
6.6	0.974	-179.85	0.44	27.70	0.007	-52.62	0.915	-173.35
6.8	0.975	-179.96	0.42	26.64	0.007	-53.37	0.918	-173.51
7.0	0.976	179.92	0.40	25.62	0.007	-54.09	0.921	-173.67
7.2	0.976	179.81	0.38	24.62	0.007	-54.78	0.924	-173.83
7.4	0.977	179.70	0.36	23.65	0.007	-55.44	0.927	-173.98
7.6	0.977	179.59	0.35	22.71	0.007	-56.06	0.929	-174.14
7.8	0.978	179.48	0.33	21.80	0.006	-56.66	0.932	-174.30
8.0	0.978	179.37	0.32	20.91	0.006	-57.23	0.934	-174.45

To download the s-parameters in s2p format, go to the [CG2H80060D](#) Product page and click on the documentation tab.

**Typical Package S-Parameters for CG2H80060D**  
**(Small Signal,  $V_{DS} = 28$  V,  $I_{DQ} = 800$  mA, magnitude/angle)**

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
0.5	0.954	-169.58	9.41	89.35	0.010	0.14	0.772	-175.06
0.6	0.954	-171.29	7.84	87.37	0.010	-1.67	0.774	-175.40
0.7	0.954	-172.52	6.71	85.64	0.010	-3.25	0.775	-175.57
0.8	0.954	-173.44	5.86	84.06	0.010	-4.67	0.777	-175.64
0.9	0.954	-174.15	5.20	82.58	0.010	-5.99	0.778	-175.64
1.0	0.955	-174.73	4.67	81.19	0.010	-7.23	0.780	-175.60
1.1	0.955	-175.19	4.23	79.84	0.010	-8.41	0.782	-175.53
1.2	0.955	-175.58	3.86	78.55	0.010	-9.55	0.783	-175.44
1.3	0.955	-175.92	3.55	77.29	0.010	-10.65	0.785	-175.34
1.4	0.956	-176.20	3.29	76.06	0.010	-11.72	0.787	-175.23
1.5	0.956	-176.45	3.06	74.86	0.009	-12.76	0.789	-175.11
1.6	0.956	-176.66	2.85	73.68	0.009	-13.78	0.791	-174.99
1.8	0.957	-177.03	2.51	71.38	0.009	-15.75	0.796	-174.75
2.0	0.958	-177.32	2.24	69.16	0.009	-17.65	0.801	-174.51
2.2	0.959	-177.57	2.01	67.01	0.009	-19.49	0.806	-174.30
2.4	0.959	-177.79	1.82	64.92	0.009	-21.25	0.811	-174.10
2.6	0.960	-177.98	1.66	62.89	0.009	-22.96	0.816	-173.93
2.8	0.961	-178.15	1.53	60.91	0.009	-24.61	0.822	-173.78
3.0	0.962	-178.30	1.40	59.00	0.009	-26.21	0.827	-173.66
3.2	0.963	-178.44	1.30	57.14	0.008	-27.75	0.832	-173.56
3.4	0.964	-178.58	1.20	55.33	0.008	-29.23	0.838	-173.48
3.6	0.965	-178.71	1.12	53.57	0.008	-30.66	0.843	-173.43
3.8	0.966	-178.83	1.05	51.87	0.008	-32.03	0.848	-173.40
4.0	0.967	-178.95	0.98	50.22	0.008	-33.36	0.854	-173.38
4.2	0.967	-179.06	0.92	48.61	0.008	-34.63	0.859	-173.38
4.4	0.968	-179.17	0.86	47.06	0.008	-35.86	0.863	-173.40
4.6	0.969	-179.28	0.81	45.55	0.007	-37.04	0.868	-173.43
4.8	0.970	-179.39	0.77	44.08	0.007	-38.17	0.873	-173.47
5.0	0.971	-179.50	0.72	42.66	0.007	-39.25	0.877	-173.53
5.2	0.971	-179.61	0.69	41.28	0.007	-40.30	0.881	-173.60
5.4	0.972	-179.71	0.65	39.95	0.007	-41.30	0.886	-173.67
5.6	0.973	-179.82	0.62	38.65	0.007	-42.25	0.890	-173.75
5.8	0.973	-179.92	0.59	37.39	0.007	-43.17	0.893	-173.84
6.0	0.974	179.98	0.56	36.16	0.006	-44.05	0.897	-173.94
6.2	0.975	179.87	0.53	34.97	0.006	-44.90	0.901	-174.04
6.4	0.975	179.77	0.51	33.82	0.006	-45.70	0.904	-174.14
6.6	0.976	179.67	0.48	32.70	0.006	-46.48	0.907	-174.25
6.8	0.976	179.57	0.46	31.60	0.006	-47.21	0.910	-174.36
7.0	0.977	179.47	0.44	30.54	0.006	-47.92	0.913	-174.48
7.2	0.977	179.37	0.43	29.51	0.006	-48.60	0.916	-174.59
7.4	0.978	179.27	0.41	28.50	0.006	-49.24	0.919	-174.71
7.6	0.978	179.17	0.39	27.52	0.006	-49.86	0.921	-174.83
7.8	0.979	179.07	0.38	26.57	0.005	-50.45	0.924	-174.95
8.0	0.979	178.97	0.36	25.64	0.005	-51.01	0.926	-175.07

To download the s-parameters in s2p format, go to the [CG2H80060D](#) Product page and click on the documentation tab.



## Product Ordering Information

Order Number	Description	Unit of Measure	Image
CG2H80060D	GaN HEMT Bare Die	Each	A photograph of a GaN HEMT bare die. It is a rectangular silicon wafer with a dark blue-green surface. Numerous gold-colored metal pads are visible along the edges and in the center, connected by a dense network of internal vias. The die is mounted on a light-colored, textured substrate.

**For more information, please contact:**

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